



MPQ18021HN-A

100V, 2.5A, High-Frequency,
Half-Bridge Gate Driver
AEC-Q100 Qualified

DESCRIPTION

The MPQ18021HN-A is a high-frequency, 100V, half-bridge, N-channel power MOSFET driver. Its low-side and high-side driver channels are controlled independently and matched with a time delay of less than 5ns. Under-voltage lockout (UVLO) on both the high-side and low-side supplies force their outputs low in the case of an insufficient supply. The integrated bootstrap diode reduces the external component count.

The MPQ18021HN-A is available in a cost-effective SOIC-8E package.

FEATURES

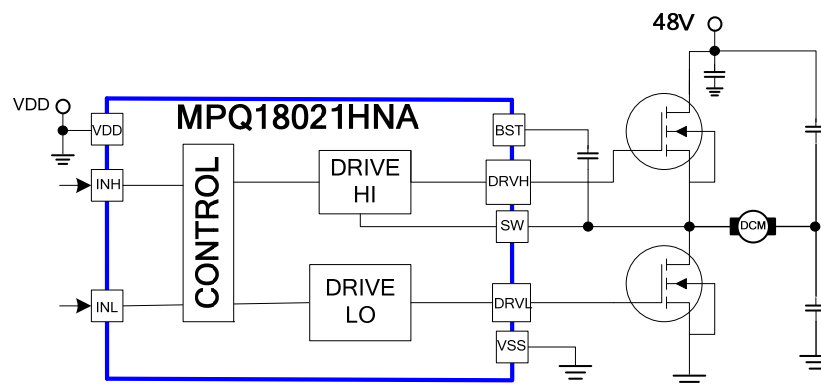
- Guaranteed Industrial / Automotive Temperature Range Limits
- Drives N-Channel MOSFET Half-Bridge
- 100V V_{BST} Voltage Range
- On-Chip Bootstrap Diode
- Typical 16ns Propagation Delay Time
- Less than 5ns Gate Drive Matching
- Drives 1nF Load with 12ns/9ns Rise/Fall Times with 12V VDD
- TTL-Compatible Input
- Less than 160 μ A Quiescent Current
- UVLO for both High-Side and Low-Side
- Available in a SOIC-8E Package
- Available in AEC-Q100 Qualified Grade 1

APPLICATIONS

- Car DC/DC Power Systems
- Half Bridge Motor Drivers

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TYPICAL APPLICATION



ORDERING INFORMATION

Part Number	Package	Top Marking
MPQ18021HN-A-AEC1	SOIC-8E	See Below

* For Tape & Reel, add suffix –Z (e.g. MPQ18021HN-A-AEC1–Z).

TOP MARKING

MP18021A

LLLLLLLL

MPSYWW

MP18021A: Part number

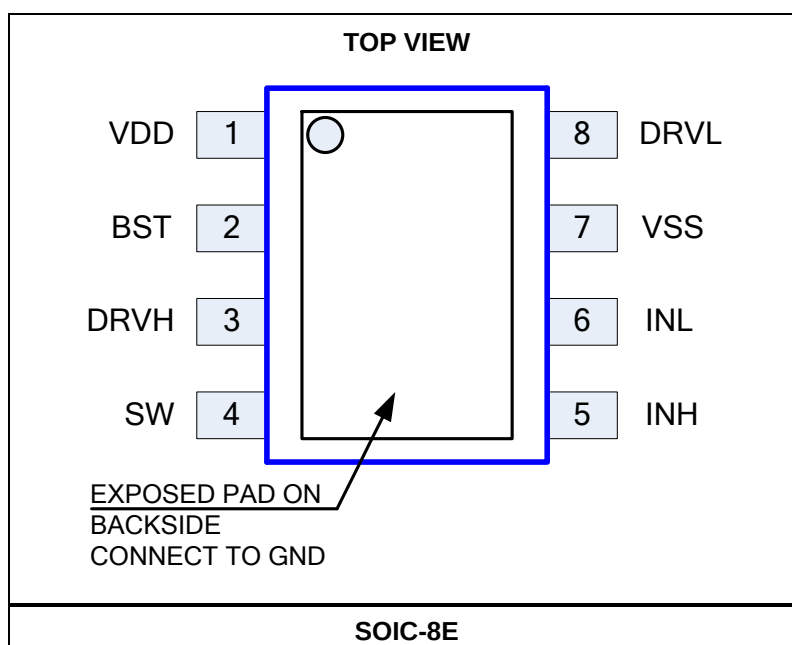
LLLLLLLL: Lot number

MPS: MPS prefix

Y: Year code

WW: Week code

PACKAGE REFERENCE



PIN FUNCTIONS

Pin #	Name	Description
1	VDD	Supply input. VDD supplies power to all of the internal circuitries. Place a decoupling capacitor to ground close to VDD to ensure a stable and clean supply.
2	BST	Bootstrap. BST is the positive power supply for the internal floating high-side MOSFET driver. Connect a bypass capacitor between BST and SW.
3	DRVH	Floating high-side driver output.
4	SW	Switching node.
5	INH	Control signal input for the floating driver.
6	INL	Control signal input for the low-side driver.
7	VSS	Chip ground. Connect the exposed pad to VSS for proper thermal operation.
Exposed Pad		
8	DRVL	Low-side driver output.

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

Supply voltage (V_{DD}) -0.3V to +18V
 SW voltage (V_{HS}) -5.0V to +110V
 BST voltage (V_{HB}) -0.3V to +110V
 BST to SW -0.3V to +18V
 DRVH to SW -0.3V to (BST - SW) + 0.3V
 DRVL to VSS -0.3V to (VDD + 0.3V)
 All other pins -0.3V to (VDD + 0.3V)
 CDM rating (AEC-Q100-011C1)
 All pins Class C6
 HBM rating (AEC-Q100-002)
 BST, DRVH Class H1B
 SW Class H1C
 Other pins Class H2
 Continuous power dissipation ($T_A = 25^\circ\text{C}$) ⁽²⁾
 2.5W
 Junction temperature 150°C
 Lead temperature 260°C
 Storage temperature -65°C to $+150^\circ\text{C}$

Recommended Operating Conditions ⁽³⁾

Supply voltage (V_{DD}) 9.0V to 16V
 SW voltage (V_{HS}) -1.0V to +100V - VDD
 SW slew rate <50V/ns
 Operation junction temp. (T_J) -40°C to $+125^\circ\text{C}$

Thermal Resistance ⁽⁴⁾ θ_{JA} θ_{JC}
 SOIC-8E 50 12 ... $^\circ\text{C/W}$

NOTES:

- Exceeding these ratings may damage the device.
- The maximum allowable power dissipation is a function of the maximum junction temperature $T_J(\text{MAX})$, the junction-to-ambient thermal resistance θ_{JA} , and the ambient temperature T_A . The maximum allowable continuous power dissipation at any ambient temperature is calculated by $P_D(\text{MAX}) = (T_J(\text{MAX}) - T_A) / \theta_{JA}$. Exceeding the maximum allowable power dissipation produces an excessive die temperature, causing the regulator to go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- Measured on JESD51-7, 4-layer PCB.

**ELECTRICAL CHARACTERISTICS**

$V_{DD} = V_{BST} - V_{SW} = 12V$, $V_{SS} = V_{SW} = 0V$, no load at DRVH and DRVL, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, typical values tested at $T_J = +25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Supply Currents						
VDD quiescent current	I _{DDQ}	INH = INL= 0		120	160	μA
VDD operating current	I _{DDO}	f _{sw} = 500kHz		2.8	3.5	mA
Floating driver quiescent current	I _{BSTQ}	INH = INL = 0		70	100	μA
Floating driver operating current	I _{BSTO}	f _{sw} = 500kHz		2.1	3	mA
Leakage current	I _{LK}	HB = SW = 100V		0.05	2.5	μA
Inputs						
INL/INH high				2.2	2.6	V
INL/INH low			1	1.5		V
INL/INH internal pull-down resistance	R _{IN}			185		kΩ
Under-Voltage Protection (UVP)						
VDD rising threshold	V _{DDR}		7.4	8.1	8.9	V
VDD hysteresis	V _{DDH}			0.5		V
(BST-SW) rising threshold	V _{BSTR}		6.5	7.1	7.7	V
(BST-SW) hysteresis	V _{BSTH}			0.55		V
Bootstrap Diode						
Bootstrap diode VF @ 100μA	V _{F1}			0.5		V
Bootstrap diode VF @ 100mA	V _{F2}			1		V
Bootstrap diode dynamic R	R _D	@ 100mA		2.5		Ω
Low Side Gate Driver						
Low-level output voltage	V _{OLL}	I _O = 100mA		0.15	0.32	V
High-level output voltage to rail	V _{OHL}	I _O = -100mA		0.45	1	V
Peak pull-up current ⁽⁵⁾	I _{OHL}	V _{LO} = 0V, V _{DD} = 12V		1.5		A
		V _{LO} = 0V, V _{DD} = 16V		2.5		A
Peak pull-down current ⁽⁵⁾	I _{OLL}	V _{LO} = V _{DD} = 12V		2.5		A
		V _{LO} = V _{DD} = 16V		3.5		A
Floating Gate Driver						
Low-level output voltage	V _{OLH}	I _O = 100mA		0.15	0.32	V
High-level output voltage to rail	V _{OHH}	I _O = -100mA		0.45	1	V
Peak pull-up current ⁽⁵⁾	I _{OHH}	V _{HO} = 0V, V _{DD} = 12V		1.5		A
		V _{HO} = 0V, V _{DD} = 16V		2.5		A
Peak pull-down current ⁽⁵⁾	I _{OLH}	V _{HO} = V _{DD} = 12V		2.5		A
		V _{HO} = V _{DD} = 16V		3.5		A
Switching spec – low-side gate driver						
Turn-off propagation delay INL falling to DRV _L falling	T _{DLFF}			16		ns
Turn-on propagation delay INL rising to DRV _L rising	T _{DLRR}			16		
DRV _L rise time		C _L = 1nF		12		ns
DRV _L fall time		C _L = 1nF		9		ns

ELECTRICAL CHARACTERISTICS (continued)

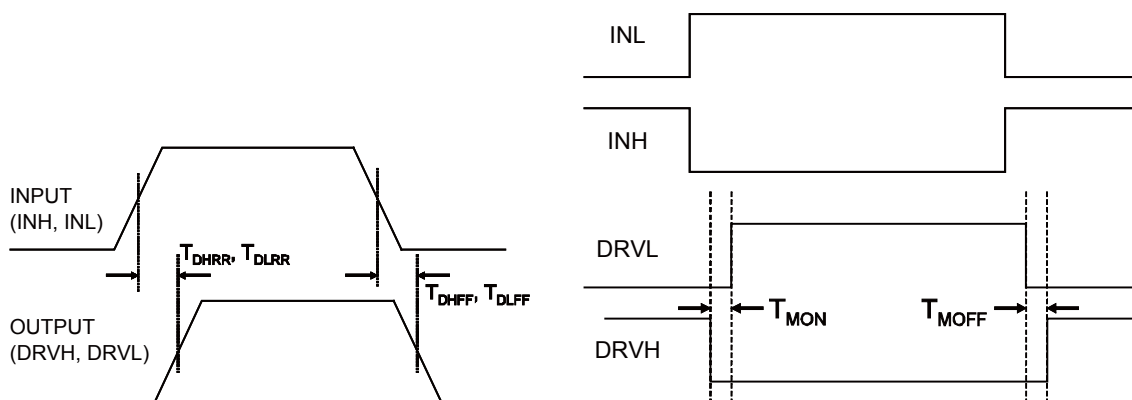
$V_{DD} = V_{BST} - V_{SW} = 12V$, $V_{SS} = V_{SW} = 0V$, no load at DRVH and DRVL, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, typical values tested at $T_J = +25^{\circ}C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Switching Spec – Floating Gate Driver						
Turn-off propagation delay INL falling to DRVH falling	T_{DHFF}			16		ns
Turn-on propagation delay INL rising to DRVH rising	T_{DHRR}			16		ns
DRVH rise time		$C_L = 1nF$		12		ns
DRVH fall time		$C_L = 1nF$		9		ns
Switching Spec – Matching						
Floating driver turn-off to low-side driver turn-on ⁽⁵⁾	T_{MON}			1	5	ns
Low-side driver turn-off to floating driver turn-on ⁽⁵⁾	T_{MOFF}			1	5	ns
Minimum input pulse width that changes the output	T_{PW}				50 ⁽⁵⁾	ns
Bootstrap diode turn-on or turn-off time	T_{BS}			10 ⁽⁵⁾		ns
Thermal shutdown ⁽⁵⁾				170		$^{\circ}C$
Thermal shutdown hysteresis ⁽⁵⁾				25		$^{\circ}C$

NOTE:

5) Guaranteed by design.

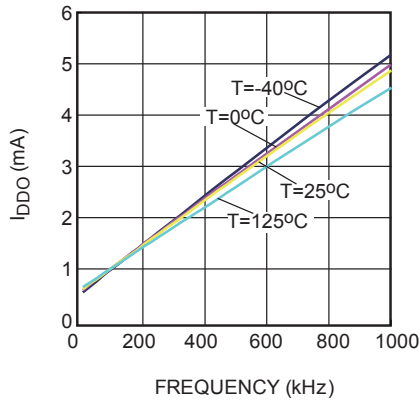
TIMING DIAGRAM



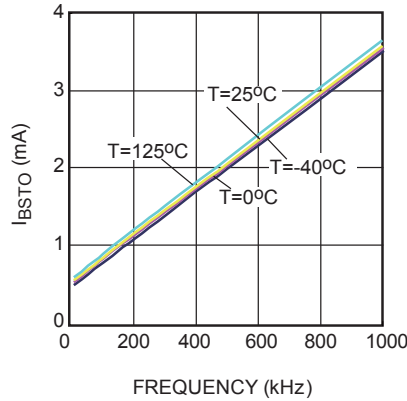
TYPICAL PERFORMANCE CHARACTERISTICS

$V_{DD} = 12V$, $V_{SS} = V_{SW} = 0V$, $T_A = 25^\circ C$, unless otherwise noted.

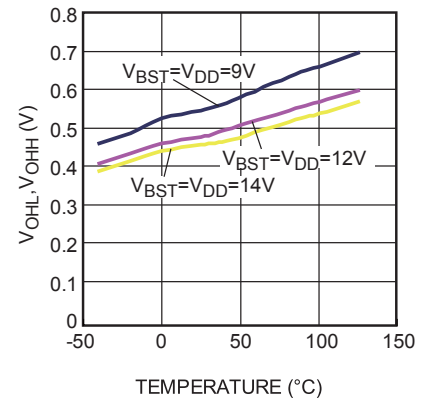
I_{DDO} Operation Current vs. Frequency



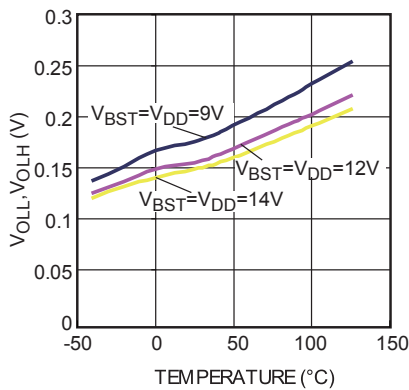
I_{BSTO} Operation Current vs. Frequency



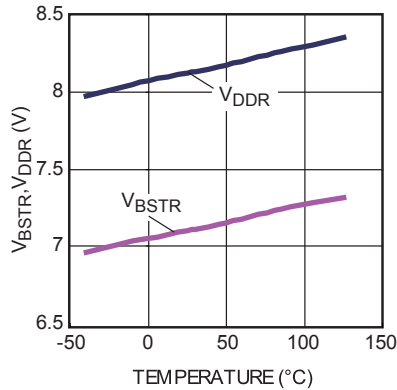
High-Level Output Voltage vs. Temperature



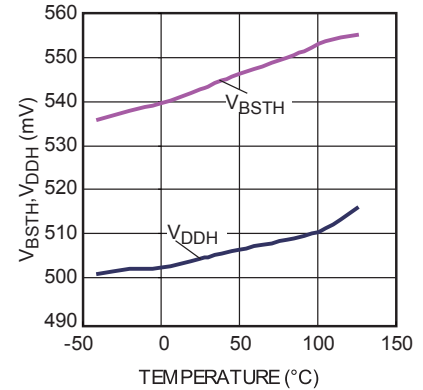
Low-Level Output Voltage vs. Temperature



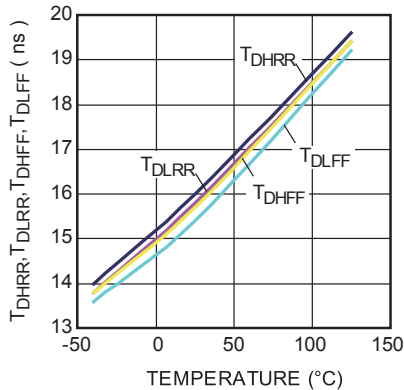
Under-Voltage Lockout Threshold vs. Temperature



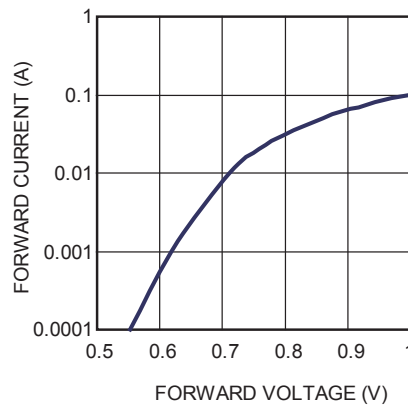
Under-Voltage Lockout Hysteresis vs. Temperature



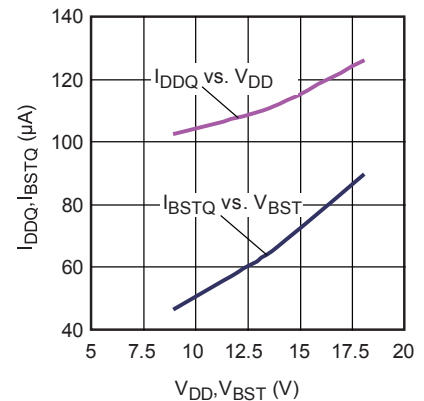
Propagation Delay vs. Temperature



Bootstrap Diode I-V Characteristics



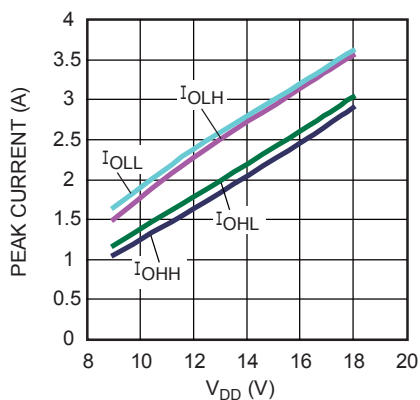
Quiescent Current vs. Voltage



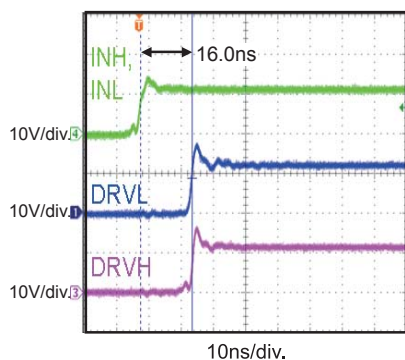
TYPICAL PERFORMANCE CHARACTERISTICS (continued)

$V_{DD} = 12V$, $V_{SS} = V_{SW} = 0V$, $T_A = 25^\circ C$, unless otherwise noted.

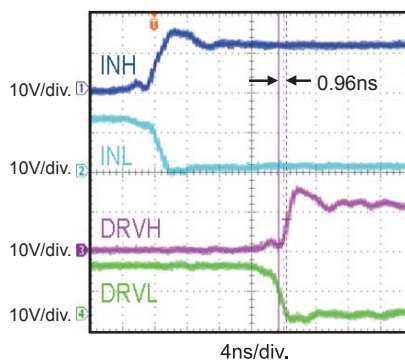
Peak Current vs.
 V_{DD} Voltage



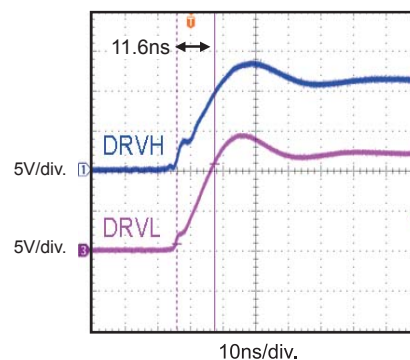
Turn-On Propagation Delay



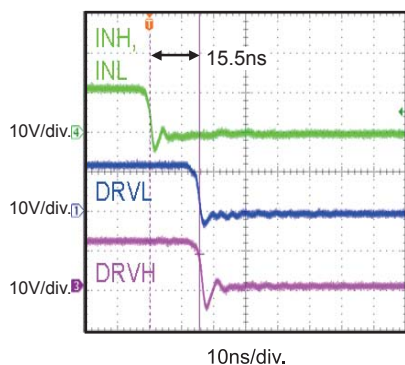
Gate Drive Matching T_{MOFF}



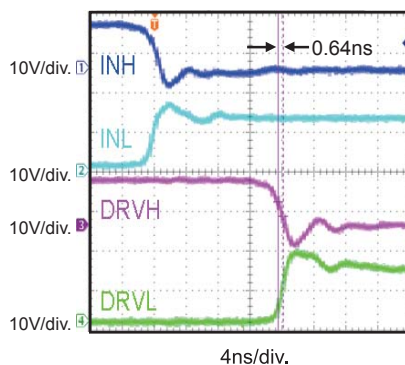
Drive Rise Time (1nF Load)



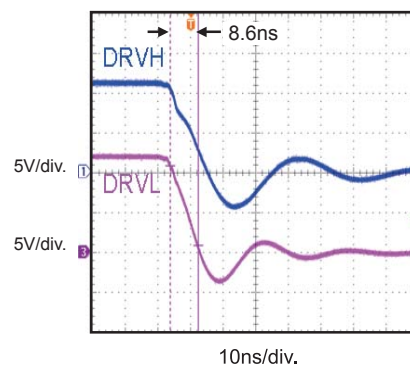
Turn-Off Propagation Delay



Gate Drive Matching T_{MON}



Drive Fall Time (1nF Load)



BLOCK DIAGRAM

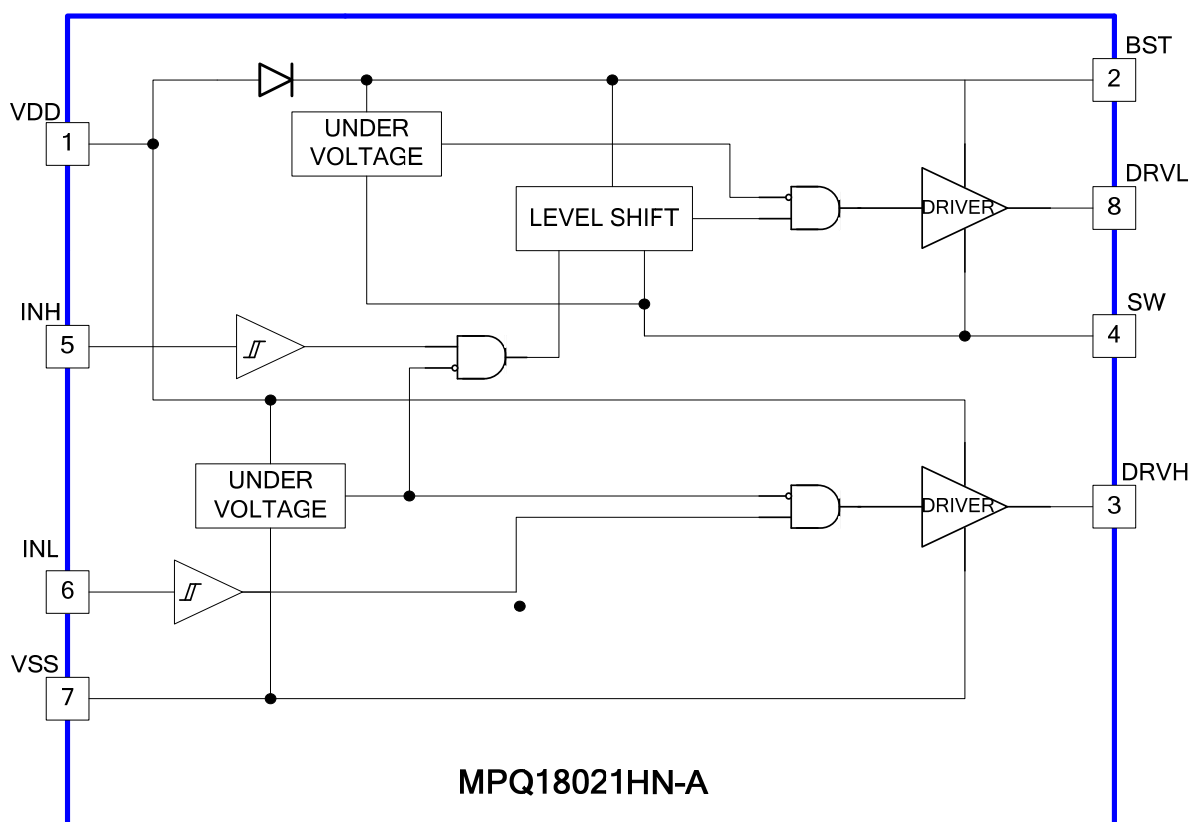


Figure 1: Functional Block Diagram

APPLICATION

The input signals of INH and INL can be controlled independently. If both INH and INL are controlling the high-side MOSFET (HS-FET) and low-side MOSFET (LS-FET) of the same bridge, shoot through can be prevented by setting a sufficient dead time between INH and INL low, and vice versa (see Figure 2). Dead time is defined as the time interval between INH low and INL low.

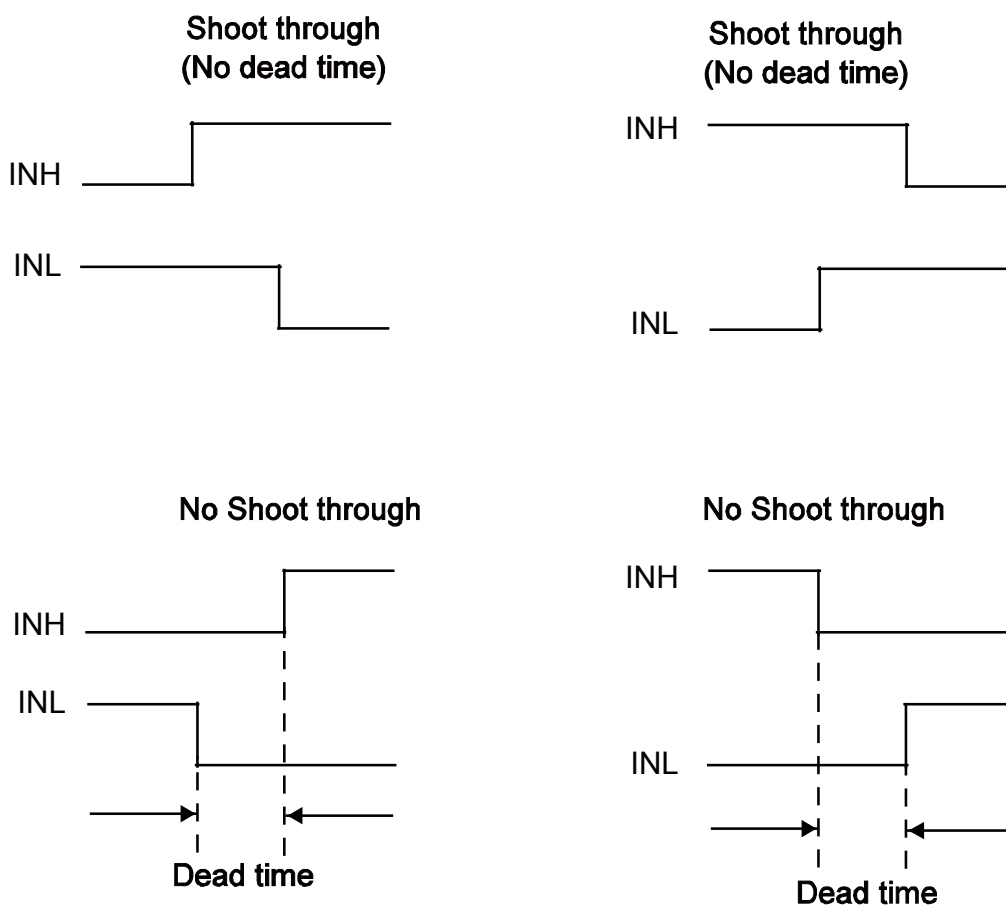


Figure 2: Shoot-Through Timing Diagram

REFERENCE DESIGN CIRCUITS

Half-Bridge Converter

In the half-bridge converter topology, the MOSFETs are driven alternately with some dead time. Therefore, INH and INL are driven

with alternating signals from the pulse-width modulation (PWM) controller. The input voltage can rise as high as 100V in this application (see Figure 3 through Figure 5).

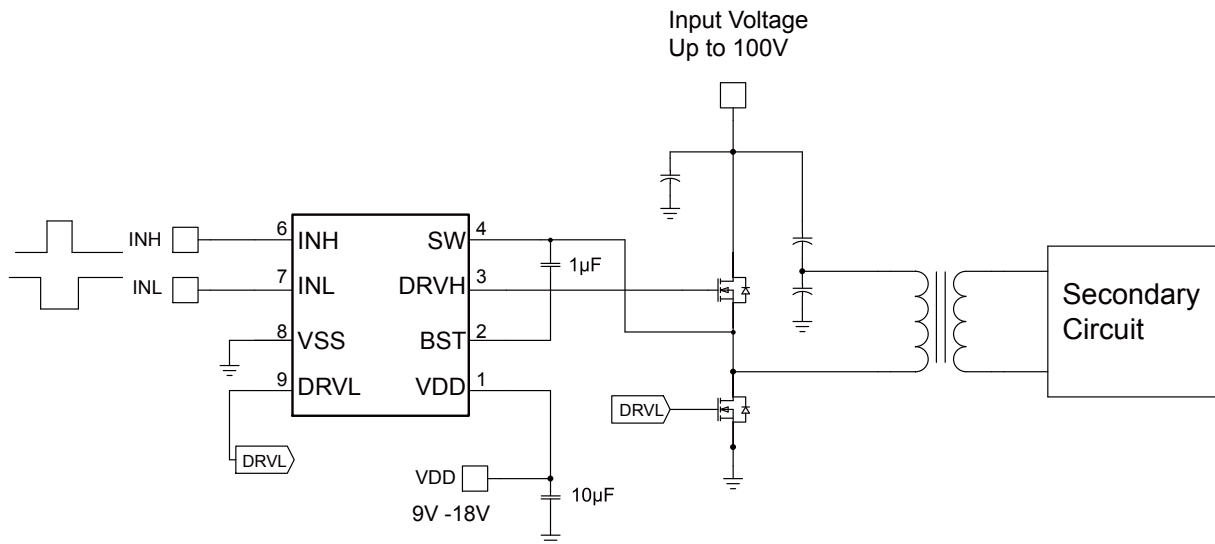


Figure 3: Half-Bridge Converter

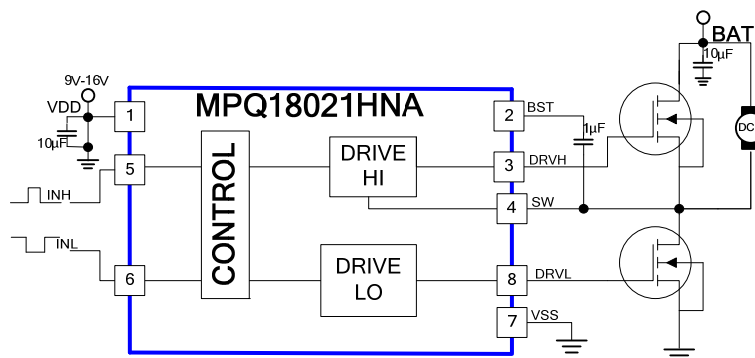


Figure 4: Half-Bridge for Unidirectional Motor

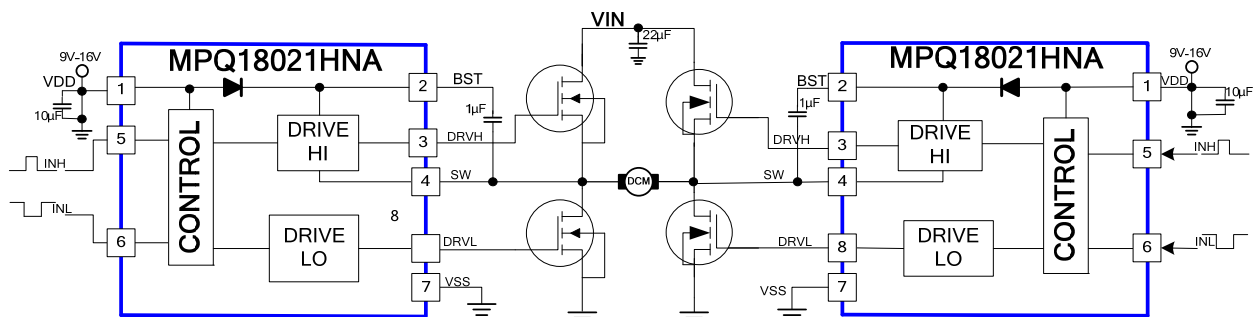
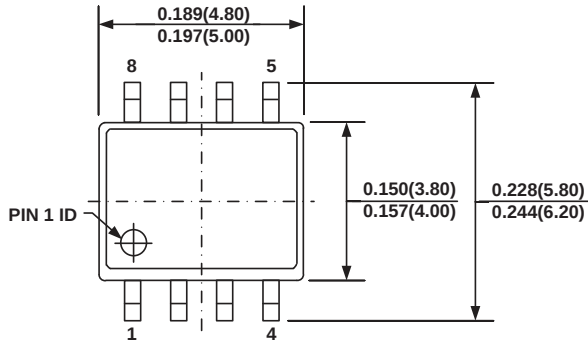


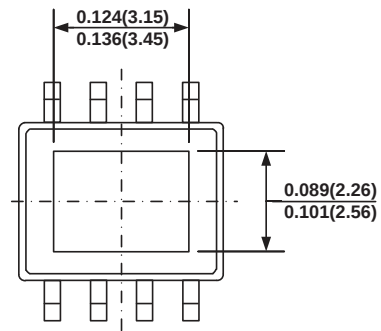
Figure 5: 2x MPQ18021HNA for One Bidirectional DC Motor

PACKAGE INFORMATION

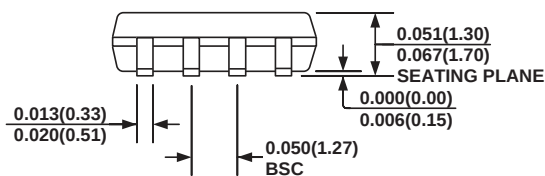
SOIC-8E



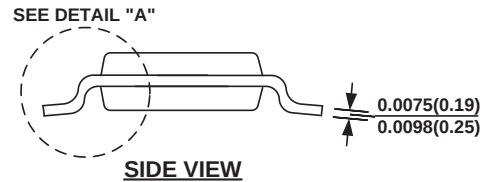
TOP VIEW



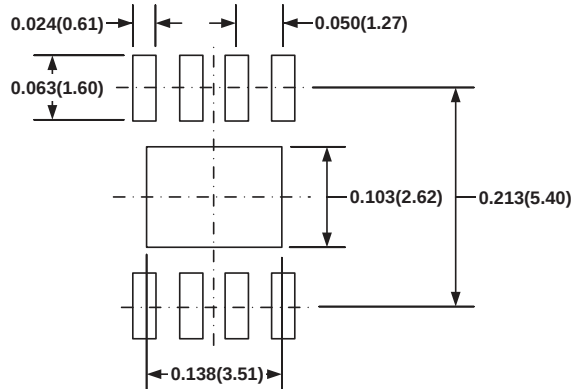
BOTTOM VIEW



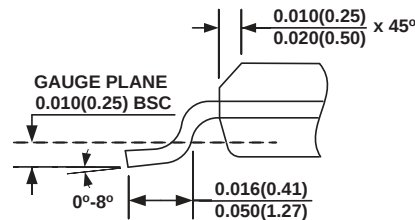
FRONT VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN



DETAIL "A"

NOTE:

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.
- 6) DRAWING IS NOT TO SCALE.

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